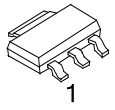
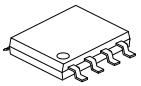
UT9435H

Power MOSFET

P-CHANNEL ENHANCEMENT MODE



SOT-223



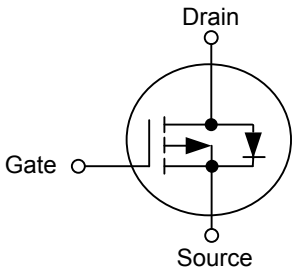
SOP-8

Lead-free: UT9435HL
Halogen-free: UT9435HG

■ DESCRIPTION

The **UTC UT9435H** provide excellent $R_{DS(ON)}$, low gate charge and fast switching speed. It has been optimized for power management applications.

■ SYMBOL



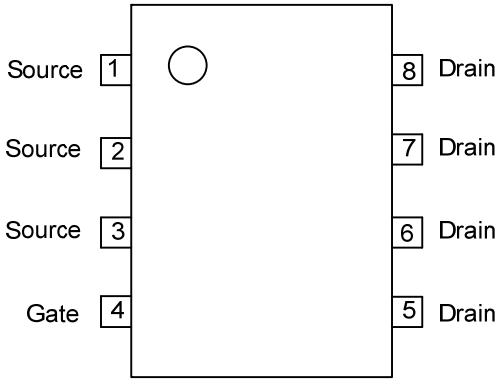
■ ORDERING INFORMATION

Ordering Number			Package	Pin Assignment								Packing
Normal	Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UT9435H-AA3-R	UT9435HL-AA3-R	UT9435HG-AA3-R	SOT-223	G	D	S	-	-	-	-	-	Tape Reel
UT9435H-S08-R	UT9435HL-S08-R	UT9435HG-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel
UT9435H-S08-T	UT9435HL-S08-T	UT9435HG-S08-T	SOP-8	S	S	S	G	D	D	D	D	Tube

UT9435HL-AA3-R
(1)Packing Type
(2)Package Type
(3)Lead Plating

(1) R: Tape Reel, T: Tube
(2) AA3: SOT-223, S08: SOP-8
(3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn

■ PIN CONFIGURATION



■ ABSOLUTE MAXIMUM RATINGS (T_A = 25℃, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 3)	Ta=125℃	I_D	±5.3	A
Pulsed Drain Current (Note 1, 2)		I_{DM}	±20	A
Power Dissipation		P_D	2.5	W
Junction Temperature		T_J	+150	℃
Storage Temperature		T_{STG}	-55 ~ +150	℃

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to-Ambient	θ_{JA}			50	℃/W

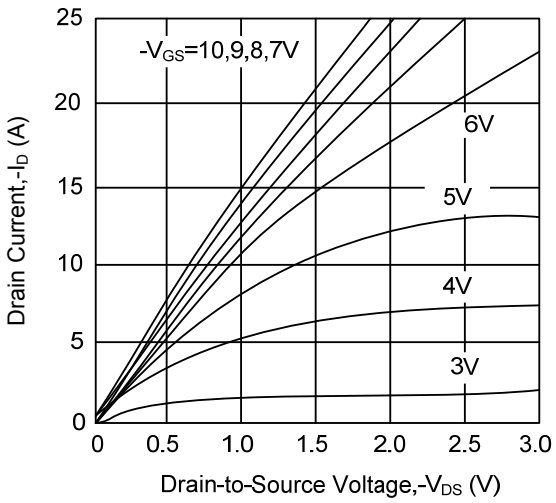
■ ELECTRICAL CHARACTERISTICS (Ta =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0 V, I_D =-250 μA	-30			V
Drain-Source Leakage Current	I_{DSS}	V_{DS} =-24 V, V_{GS} =0 V			-1	μA
Gate-Source Leakage Current	I_{GSS}	V_{DS} =0 V, V_{GS} = ±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS} =V_{GS}, I_D =-250 μA	-1		-3	V
Drain-Source On-State Resistance (Note 2)	$R_{DS(ON)}$	V_{GS} =-10V, I_D =-5.3A		44	50	mΩ
		V_{GS} =-4.5V, I_D =-4.2A		74	90	mΩ
On State Drain Current	$I_{D(ON)}$	V_{DS} = -5V, V_{GS} =-10V	-20			A
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{DS} =-15V, V_{GS} =0V, f=1.0MHz		1040		pF
Output Capacitance	C_{OSS}			420		pF
Reverse Transfer Capacitance	C_{RSS}			150		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time (Note 2)	$t_{D(ON)}$	V_{DD} =-15V, I_D=-1A, V_{GEN} =-10V, R_G =6 Ω		19	26	ns
Turn-ON Rise Time	t_R			9	13	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			74	105	ns
Turn-OFF Fall Time	t_F			36	50	ns
Total Gate Charge (Note 2)	Q_G	V_{DS} =-15V, V_{GS} =-10V, I_D =-4.6 A		22.5	29	nC
Gate-Source Charge	Q_{GS}			2		nC
Gate-Drain Charge	Q_{GD}			6		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	V_{GS} =0 V, I_S =-5.3 A		-0.84	-1.3	V

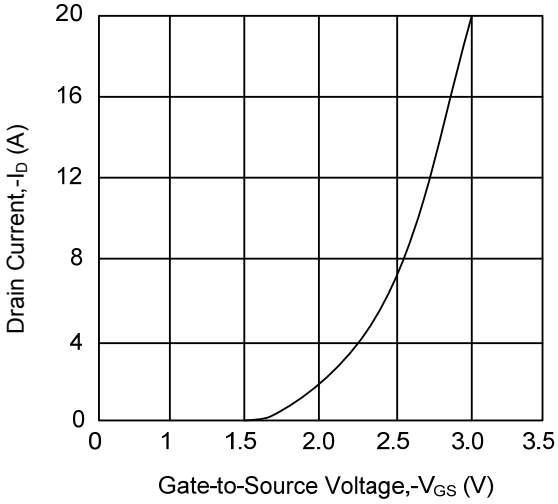
Notes: 1. Pulse width limited by $T_{J(MAX)}$
2. Pulse width ≤300us, duty cycle ≤2%.
3. Surface mounted on 1 in^2 copper pad of FR4 board

■ TYPICAL CHARACTERISTICS

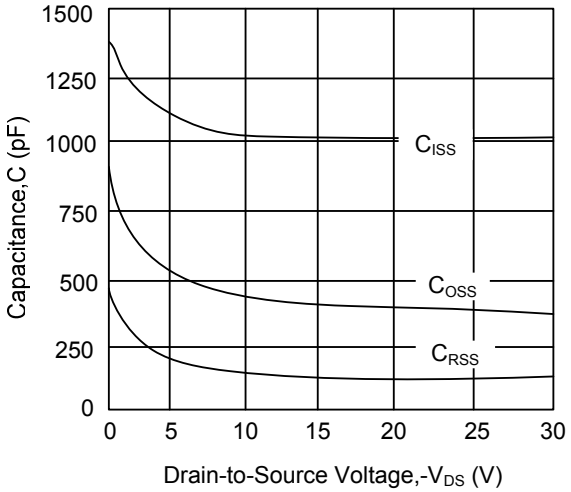
Output Characteristics



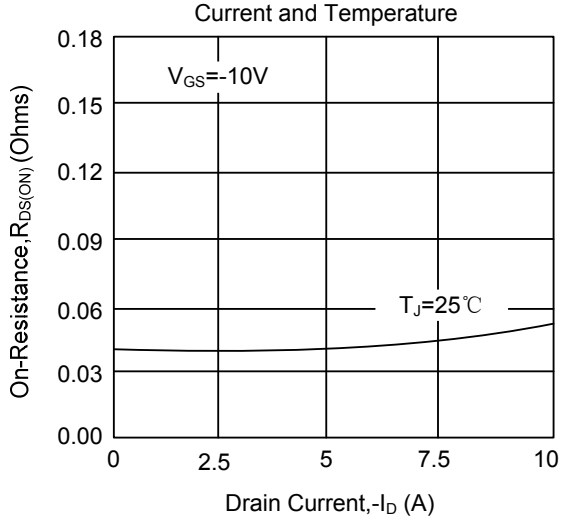
Transfer Characteristics



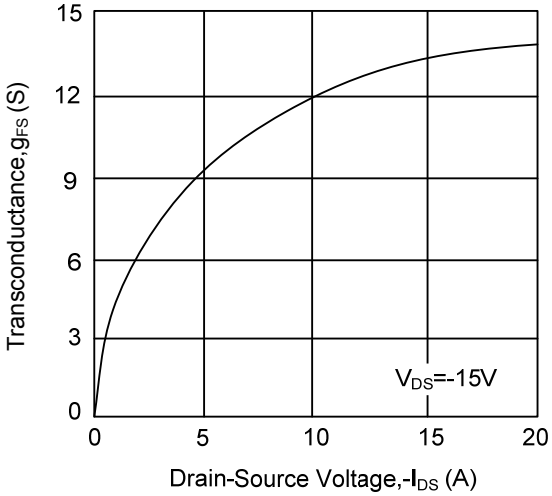
Capacitance



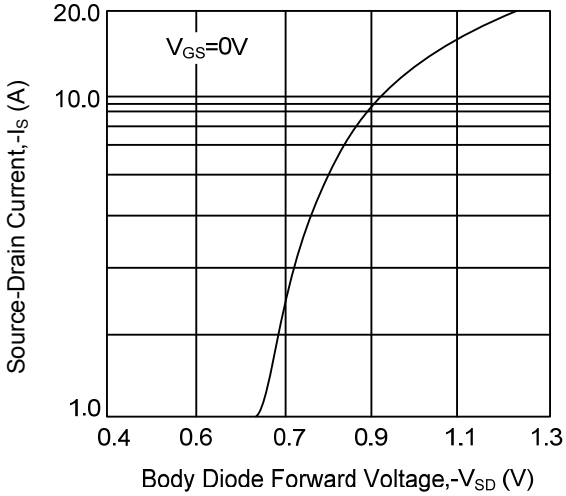
On-Rseistance Variation with Drain Current and Temperature



Transconductance Variation with Drain Current



Body Diode Forward Voltage Variation with Source Currrent



■ TYPICAL CHARACTERISTICS(Cont.)